

# SOT23 SILICON PLANAR HIGH SPEED SWITCHING DIODE

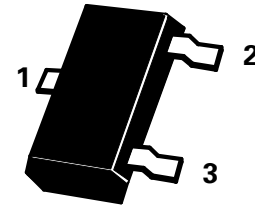
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## FMMD914

### DIODE PIN CONNECTION



PARTMARKING DETAIL - 5D



SOT23

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Working Peak Reverse Voltage	$V_{RWM}$	75	V
Average Rectified Forward Current at $T_{amb}=25^{\circ}C$	$I_{F(AV)}$	75	mA
Repetitive Peak Forward Current	$I_{FRM}$	225	mA
Power Dissipation at $T_{amb} = 25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	$V_{BR}$	75		V	$I_R=100\mu A$
Forward Voltage	$V_F$		1	V	$I_F=10mA$
Static Reverse Current	$I_R$		25 50	nA $\mu A$	$V_R=20V$ $V_R=20V, T_{amb}=150^{\circ}C$
Reverse Recovery Time	$t_{rr}$		8	ns	$I_F=I_{RM}=10mA, I_{RR}=1mA$ $R_L=100\Omega$
			4	ns	$I_F=10mA, I_{RR}=1mA, V_R=6V$ $R_L=100\Omega$
Total Capacitance	$C_T$		4	pF	$V_R=0, f=1MHz$
Forward Recovery Voltage	$V_{FM(REC)}$		2.5	V	$I_F=50mA, R_L=50\Omega$
Rectification Efficiency	$\eta_r$	45		%	$V_R=2V, R_L=5k\Omega, C_L=20pF$ $Z_{source}=50\Omega, f=100MHz$

Spice parameter data is available upon request for this device